

## Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-60	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current	I <sub>C</sub>	-600	mA

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	$P_{D}$	150	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	833	°C/W
Operating and Storage Temperature Range	$T_J$ , $T_{STG}$	-55 to +150	°C

## ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

Notes: 5. F

- 5. For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

# **Thermal Characteristics and Derating Information**

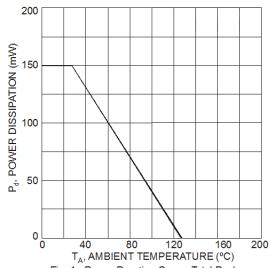


Fig. 1, Power Derating Curve, Total Package



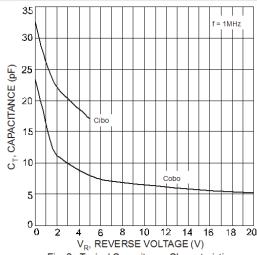
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

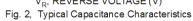
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)					
Collector-Base Breakdown Voltage	$BV_{CBO}$	-60	_	V	$I_C = -10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	-60	_	V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-5	_	V	$I_E = -10\mu A, I_C = 0$
Collector Base Cutoff Current	Ісво		-10	nA	$V_{CB} = -50V, I_{E} = 0$
Collector Base Cutoff Current			-10	μΑ	$V_{CB} = -50V$ , $I_E = 0$ , $T_A = +125$ °C
Collector Cutoff Current	I <sub>CEX</sub>		-50	nA	$V_{CE} = -30V$ , $V_{EB(OFF)} = -0.5V$
Base Cutoff Current	$I_{BL}$	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -0.5V$
ON CHARACTERISTICS (Note 7)					
		75	_		$I_C = -100uA, V_{CE} = -10V$
		100	_		$I_C = -1 \text{mA}, V_{CE} = -10 \text{V}$
DC Current Gain	h <sub>FE</sub>	100	_	_	$I_C = -10 \text{mA}, V_{CE} = -10 \text{V}$
		100	300		$I_C = -150 \text{mA}, V_{CE} = -10 \text{V}$
		50	_		$I_C = -500 \text{mA}, V_{CE} = -10 \text{V}$
Collector-Emitter Saturation Voltage	V <sub>CE</sub> (SAT)	n —	-0.4	V	$I_C = -150 \text{mA}, I_B = -15 \text{mA}$
Collector-Emitter Saturation Voltage			-1.6		$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>		1.3	V	$I_C = -150 \text{mA}, I_B = -15 \text{mA}$
ů	V BE(SAT)		2.6	v	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
SMALL SIGNAL CHARACTERISTICS				•	
Output Capacitance	Сово	_	8	pF	$V_{CB} = -10V$ , $f = 1.0MHz$ , $I_E = 0$
Input Capacitance	C <sub>IBO</sub>	_	30	pF	$V_{EB} = -2V$ , $f = 1.0MHz$ , $I_{C} = 0$
Current Gain-Bandwidth Product	f⊤	200	_	MHz	$V_{CE} = -20V, I_{C} = -50mA,$ f = 100MHz
SWITCHING CHARACTERISTICS					
Turn-On Time	t <sub>ON</sub>	1	45	ns	V <sub>CC</sub> = -30V, I <sub>C</sub> = -150mA,
Delay Time	t <sub>D</sub>	_	10	ns	$I_{B1} = -15 \text{mA}$
Rise Time	t <sub>R</sub>	_	40	ns	IBI — - IOIIIV
Turn-Off Time	toff	1	100	ns	V <sub>CC</sub> = -6V, I <sub>C</sub> = -150mA,
Storage Time	ts	_	80	ns	$I_{B1} = I_{B2} = -15 \text{mA}$
Fall Time	t <sub>F</sub>	_	30	ns	IB1 - IB7 - 10111V

Note: 7. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)





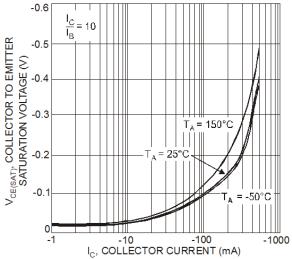
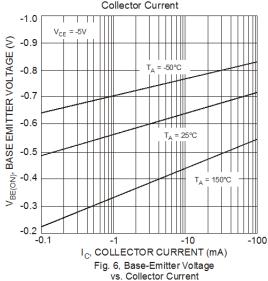


Fig. 4, Collector-Emitter Saturation Voltage vs. Collector Current



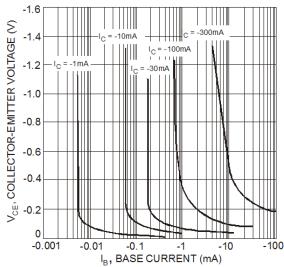
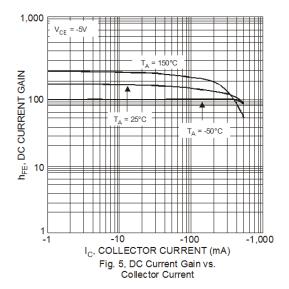


Fig. 3, Typical Collector Saturation Region



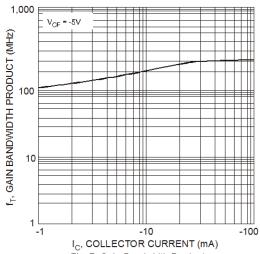


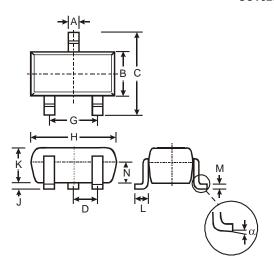
Fig. 7, Gain Bandwidth Product vs. Collector Current



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT523**

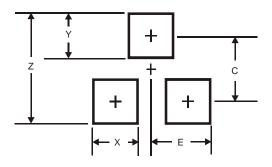


SOT523				
Dim	Min	Max	Тур	
Α	0.15	0.30	0.22	
В	0.75	0.85	0.80	
С	1.45	1.75	1.60	
D			0.50	
G	0.90	1.10	1.00	
Н	1.50	1.70	1.60	
J	0.00	0.10	0.05	
K	0.60	0.80	0.75	
L	0.10	0.30	0.22	
M	0.10	0.20	0.12	
N	0.45	0.65	0.50	
α	0°	8°		
All Dimensions in mm				

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT523



Dimensions	Value (in mm)
Z	1.8
Х	0.4
Y	0.51
С	1.3
Е	0.7



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